

STGB3HF60HD, STGD3HF60HDT4, STGF3HF60HD, STGP3HF60HD

4.5 A, 600 V very fast IGBT with Ultrafast diode

Datasheet - production data

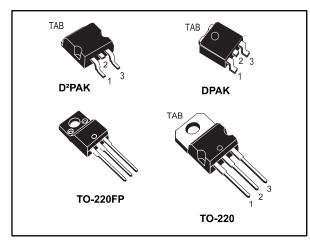
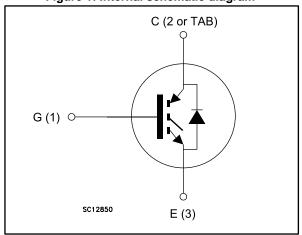


Figure 1: Internal schematic diagram



Features

- Minimal tail current
- Low conduction and switching losses
- Ultrafast soft recovery antiparallel diode

Applications

Motor drive

Description

These devices are based on a new advanced planar technology concept to yield an IGBT with more stable switching performance (E_{off}) versus temperature, as well as lower conduction losses.

Table 1: Device summary

Order code	Marking	Package	Packing
STGB3HF60HD	GB3HF60HD	D²PAK	Tape and reel
STGD3HF60HDT4	GD3HF60HD	DPAK	Tape and reel
STGF3HF60HD	GF3HF60HD	TO-220FP	Tube
STGP3HF60HD	GP3HF60HD	TO-220	Tube

September 2016 DocID17690 Rev 5 1/26

Contents

1	Electric	al ratings	3
2		al characteristics	
	2.1	Electrical characteristics (curves)	7
3	Test cir	cuits	
4	Packag	e information	11
	4.1	D ² PAK (TO-263) package information	11
	4.2	D ² PAK (TO-263) packing information	14
	4.3	DPAK (TO-252) type A package information	16
	4.4	DPAK (TO-252) packing information	19
	4.5	TO-220FP package information	21
	4.6	TO-220 type A package information	23
5	Revisio	n history	25



1 Electrical ratings

Table 2: Absolute maximum ratings

			Value		
Symbol	Parameter	DPAK	D ² PAK TO-220	TO-220FP	Unit
Vces	Collector-emitter voltage (V _{GE} = 0)		600		V
Ic ⁽¹⁾	Continuous collector current at T _C = 25 °C		7.5		Α
Ic ⁽¹⁾	Continuous collector current at T _C = 100 °C		4.5		Α
Icl ⁽²⁾	Turn-off latching current	18		Α	
I _{CP} ⁽³⁾	Pulsed collector current	18			Α
V _{GE}	Gate-emitter voltage		± 20		V
l _F	Diode RMS forward current at T _C = 25 °C		10		Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms}$ sinusoidal	25		Α	
Ртот	Total dissipation at T _C = 25 °C	38 18		W	
T _{STG}	Storage temperature range		55 to 450		°C
Tj	Operating junction temperature range	- 55 to 150		OU	C

Notes:

⁽¹⁾Calculated according to the iterative formula:

$$I_{C}(T_{C}) = \frac{T_{j(max)} - T_{C}}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_{C}(T_{C}))}$$

Table 3: Thermal data

Symbol	Parameter	DPAK	D ² PAK TO-220	TO-220FP	Unit	
D	Thermal resistance junction-case IGBT	3.3		6.9	°C/W	
R _{thj-case}	Thermal resistance junction-case diode	5		8	°C/W	
R _{thj-amb}	Thermal resistance junction-ambient	100 62.5		62.5	°C/W	

 $^{^{(2)}}V_{clamp}$ = 80 %, (Vces), T_{j} = 150 °C, R_{G} = 10 $\Omega,$ V_{GE} = 15 V.

 $^{^{(3)}}$ Pulse width limited by maximum junction temperature range.

2 Electrical characteristics

(T_j=25 °C unless otherwise specified).

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _(BR) CES	Collector-emitter breakdown voltage (V _{GE} = 0)	Ic = 1 mA	600			V
		$V_{GE} = 15 \text{ V}, I_{C} = 0.5 \text{ A},$ $T_{j} = 125 \text{ °C}$		1.4		
V _{CE(sat)}	Collector-emitter saturation voltage	V _{GE} = 15 V, I _C = 1.5 A		2.45	2.95	V
		$V_{GE} = 15 \text{ V}, I_{C} = 1.5 \text{ A},$ $T_{j} = 125 \text{ °C}$		1.85		
$V_{\text{GE(th)}}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 250 \mu A$	3.75		5.75	V
	Callagtar and off anymout	V _{CE} = 600 V			250	μΑ
Ices	Collector cut-off current (V _{GE} = 0)	$V_{CE} = 600 \text{ V},$ $T_{j} = 125 \text{ °C}$			1	mA
Iges	Gate-emitter leakage current (VcE = 0)	V _{GE} = ± 20 V			± 100	nA
g fs	Forward transconductance	$V_{CE} = 15 \text{ V}, I_{C} = 1.5 \text{ A}$		1.5		S

Table 5: Dynamic electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Cies	Input capacitance		•	152	-	pF
Coes	Output capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0	•	14	-	pF
Cres	Reverse transfer capacitance	VGL - V	•	3	-	pF
Qg	Total gate charge	Vce = 480 V,	•	12	-	nC
Q_ge	Gate-emitter charge	Ic = 1.5 A, V _{GE} = 15 V	•	2	-	nC
Qgc	Gate-collector charge	(see Figure 18: " Gate charge test circuit")	-	6	-	nC



Table 6: Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	Vcc = 400 V, Ic = 1.5 A	-	11	-	ns
tr	Current rise time	R_{G} = 100 Ω , V_{GE} = 15 V	-	4	-	ns
(di/dt)on	Turn-on current slope	(see Figure 17: " Test circuit for inductive load switching"Figure 19: " Switching waveform")	1	285	-	A/µs
t _{d(on)}	Turn-on delay time	Vcc = 400 V, Ic = 1.5 A	-	10	-	ns
tr	Current rise time	$R_G = 100 \Omega, V_{GE} = 15 V,$	•	5	-	ns
(di/dt)on	Turn-on current slope	T _j = 125 °C (see Figure 17: " Test circuit for inductive load switching"Figure 19: " Switching waveform")		265	ı	A/μs
tr(Voff)	Off voltage rise time	V _{CC} = 400 V, I _C = 1.5 A,	•	26	-	ns
td(off)	Turn-off delay time	$R_{GE} = 100 \Omega, V_{GE} = 15 V$	•	60	-	ns
t _f	Current fall time	(see Figure 17: " Test circuit for inductive load switching"Figure 19: " Switching waveform")	1	50	-	ns
tr(Voff)	Off voltage rise time	Vcc = 400 V, Ic = 1.5 A,	-	64	-	ns
td(off)	Turn-off delay time	$R_{GE} = 100 \Omega, V_{GE} = 15 V,$		69	-	ns
t _f	Current fall time	T _j = 125 °C (see Figure 17: " Test circuit for inductive load switching"Figure 19: " Switching waveform")	-	71	-	ns

Table 7: Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
E _{on} ⁽¹⁾	Turn-on switching energy	$V_{CC} = 400 \text{ V}, I_{C} = 1.5 \text{ A}$ $R_{G} = 100 \Omega, V_{GE} = 15 \text{ V}$	-	19	1	μJ
E _{off} ⁽²⁾ E _{ts}	Turn-off switching energy	R _G = 100 Ω, V _{GE} = 15 V (see Figure 17: " Test circuit for inductive load switching"Figure 19: " Switching waveform")		12	-	μJ
Ets	Total switching energy			31	ı	μJ
E _{on} ⁽¹⁾	Turn-on switching energy	$V_{CC} = 400 \text{ V}, I_C = 1.5 \text{ A}$ $R_G = 100 \Omega, V_{GE} = 15 \text{ V},$	-	38	ı	μJ
E _{off} ⁽²⁾	Turn-off switching energy	T _j = 125 °C (see Figure 17: " Test circuit for inductive load	-	35		μJ
Ets	Total switching energy	switching"Figure 19: " Switching waveform")	-	73	-	μJ

Notes:



⁽¹⁾Eon is the turn-on energy when a typical diode is used in the test circuit in *Figure 17: " Test circuit for inductive load switching"*. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs and diode are at the same temperature (25 °C and 125 °C).

 $[\]ensuremath{^{(2)}}\mbox{Turn-off}$ energy include also the tail of the collector current.

Table 8: Collector-emitter diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	F	I _F = 1.5 A	-	1.4	1.8	.,
V _F	Forward on-voltage	I _F = 1.5 A, T _j = 125 °C	-	1.15		V
t _{rr}	Reverse recovery time	1. 4.5.4.1/40.1/.	-	85		ns
Qrr	Reverse recovery charge	$I_F = 1.5 \text{ A}, V_R = 40 \text{ V},$ $di/dt = 100 \text{ A/}\mu\text{s}$	-	124		nC
I _{rrm}	Reverse recovery current	(see Figure 20: " Diode reverse recovery waveform")	-	3		Α
t _{rr}	Reverse recovery time	1. 4.5.4.7. 40.7.	-	114		ns
Qrr	Reverse recovery charge	$I_F = 1.5 \text{ A}, V_R = 40 \text{ V},$ $T_j = 125 \text{ °C}, \text{ di/dt} = 100 \text{ A/µs}$	-	194		nC
Irrm	Reverse recovery current	(see Figure 20: " Diode reverse recovery waveform")	-	3.5		Α

2.1 Electrical characteristics (curves)

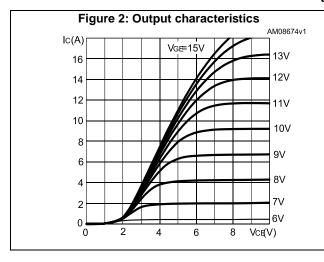


Figure 3: Output characteristic details

AM08675v1

4.0

3.5

3.0

2.5

2.0

1.5

1.0

0.5

0

1 2 3 4 VCt(V)

Figure 4: Transfer characteristics

AM08676v1

IC(A)

16

14

12

10

8

6

4

2

0

0

2

4

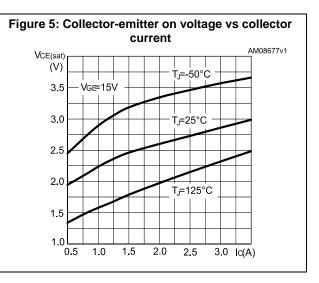
6

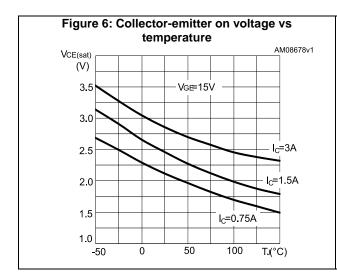
8

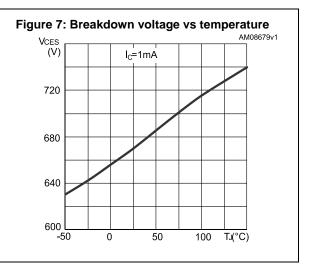
10

12

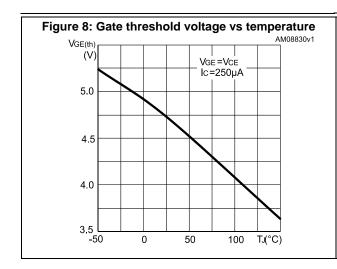
VGE(V)

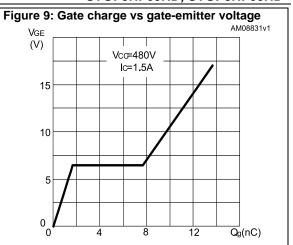


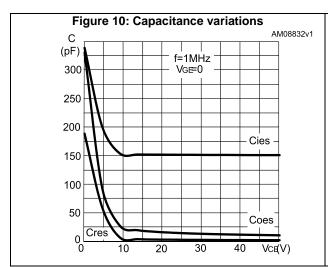


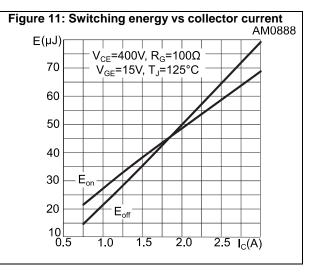


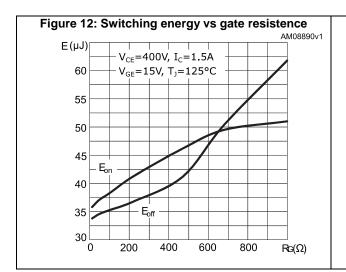
47/

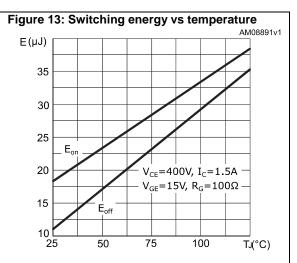




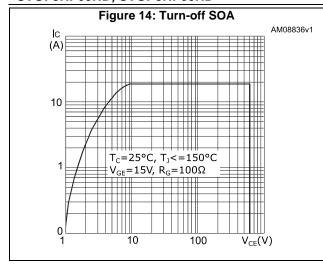


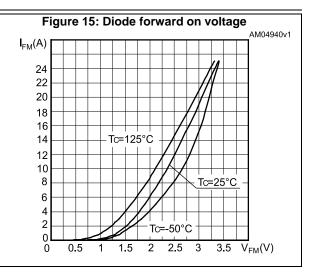


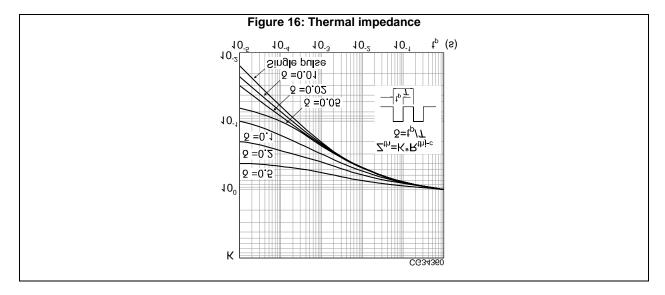




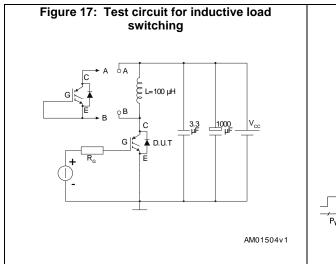
577

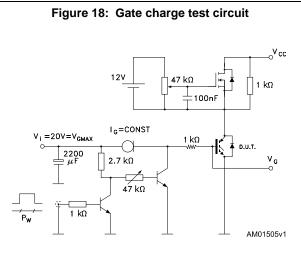


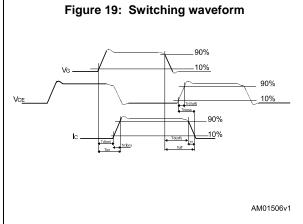


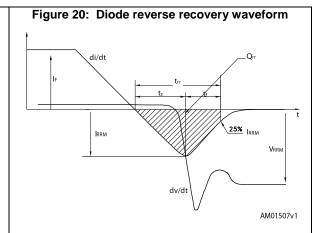


3 Test circuits









Downloaded from Arrow.com.

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 D²PAK (TO-263) package information

E1c2-<u>E/2</u>, *L1* D1 THERMAL PAD *b2* SEATING PLANE COPLANARITY A 1 R 0.25 GAUGE PLANE V2 0079457_A_rev22

Figure 21: D²PAK (TO-263) type A package outline

47/

DocID17690 Rev 5

11/26

Table 9: D²PAK (TO-263) type A package mechanical data

mm						
Dim.	Min.	Тур.	Max.			
A	4.40	·	4.60			
A1	0.03		0.23			
b	0.70		0.93			
b2	1.14		1.70			
С	0.45		0.60			
c2	1.23		1.36			
D	8.95		9.35			
D1	7.50	7.75	8.00			
D2	1.10	1.30	1.50			
E	10		10.40			
E1	8.50	8.70	8.90			
E2	6.85	7.05	7.25			
е		2.54				
e1	4.88		5.28			
Н	15		15.85			
J1	2.49		2.69			
L	2.29		2.79			
L1	1.27		1.40			
L2	1.30		1.75			
R		0.4				
V2	0°		8°			

9.75

16.9

1.6

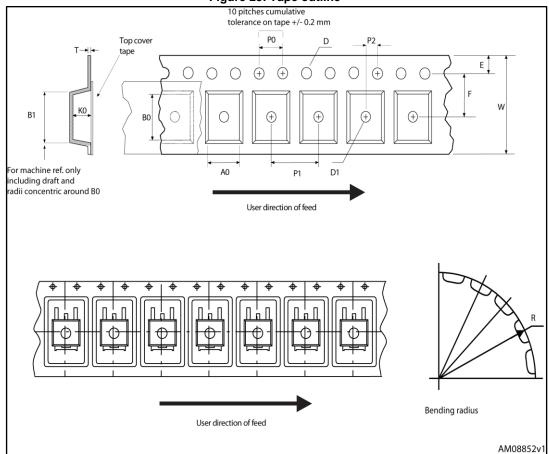
2.54

5.08

Figure 22: D²PAK (TO-263) recommended footprint (dimensions are in mm)

4.2 D²PAK (TO-263) packing information

Figure 23: Tape outline



40mm min. access hole at slot location D С G measured Tape slot at hub in core for Full radius tape start 2.5mm min.width AM06038v1

Figure 24: Reel outline

Table 10: D²PAK tape and reel mechanical data

	Tape		Reel		
Dim	m	ım	Dim	mm	
Dim.	Min.	Max.	Dim.	Min.	Max.
A0	10.5	10.7	А		330
В0	15.7	15.9	В	1.5	
D	1.5	1.6	С	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	Т		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base q	uantity	1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
Т	0.25	0.35			
W	23.7	24.3			

4.3 DPAK (TO-252) type A package information

Figure 25: DPAK (TO-252) type A package outline

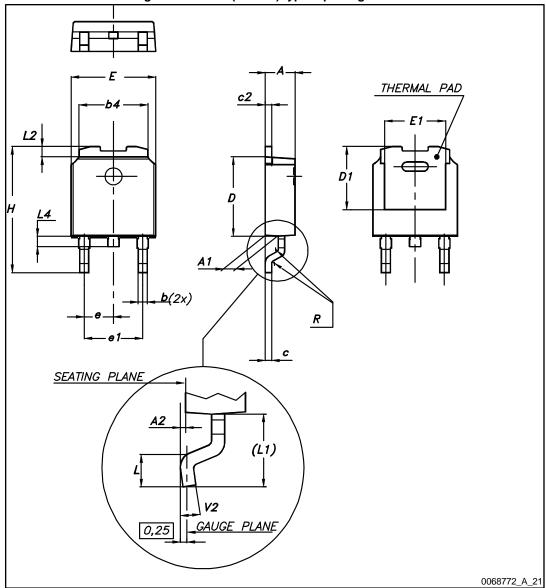


Table 11: DPAK (TO-252) type A mechanical data

Table 11: DPAK (TO-252) type A mechanical data						
Dim		mm				
Dim.	Min.	Тур.	Max.			
А	2.20		2.40			
A1	0.90		1.10			
A2	0.03		0.23			
b	0.64		0.90			
b4	5.20		5.40			
С	0.45		0.60			
c2	0.48		0.60			
D	6.00		6.20			
D1	4.95	5.10	5.25			
Е	6.40		6.60			
E1	4.60	4.70	4.80			
е	2.16	2.28	2.40			
e1	4.40		4.60			
Н	9.35		10.10			
L	1.00		1.50			
(L1)	2.60	2.80	3.00			
L2	0.65	0.80	0.95			
L4	0.60		1.00			
R		0.20				
V2	0°		8°			

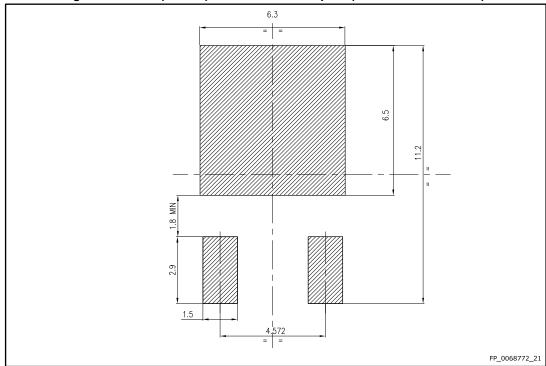
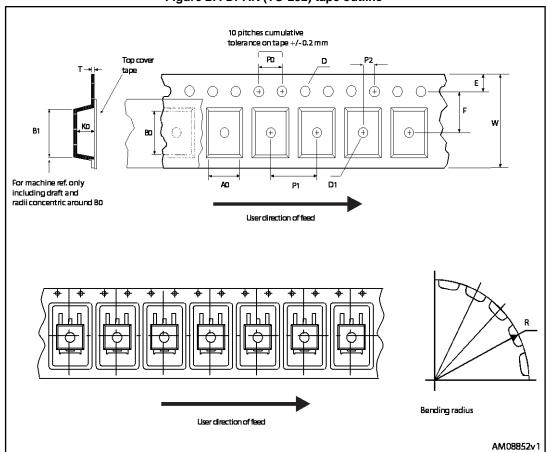


Figure 26: DPAK (TO-252) recommended footprint (dimensions are in mm)



4.4 DPAK (TO-252) packing information

Figure 27: DPAK (TO-252) tape outline



40mm min. access hole at slot location

Tape slot in core for tape start 2.5mm min.width

AM06038v1

Figure 28: DPAK (TO-252) reel outline

Table 12: DPAK (TO-252) tape and reel mechanical data

Таре			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.	DIM.	Min.	Max.
A0	6.8	7	Α		330
B0	10.4	10.6	В	1.5	
B1		12.1	С	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
Е	1.65	1.85	N	50	
F	7.4	7.6	Т		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base	qty.	2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
Т	0.25	0.35			
W	15.7	16.3			

4.5 TO-220FP package information

Figure 29: TO-220FP package outline

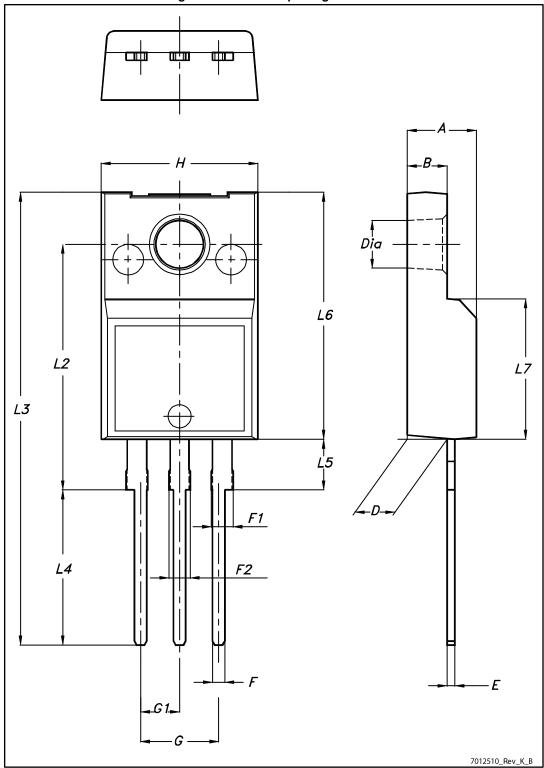


Table 13: TO-220FP package mechanical data

mm					
Dim.	mm				
	Min.	Тур.	Max.		
A	4.4		4.6		
В	2.5		2.7		
D	2.5		2.75		
Е	0.45		0.7		
F	0.75		1		
F1	1.15		1.70		
F2	1.15		1.70		
G	4.95		5.2		
G1	2.4		2.7		
Н	10		10.4		
L2		16			
L3	28.6		30.6		
L4	9.8		10.6		
L5	2.9		3.6		
L6	15.9		16.4		
L7	9		9.3		
Dia	3		3.2		

4.6 TO-220 type A package information

Figure 30: TO-220 type A package outline

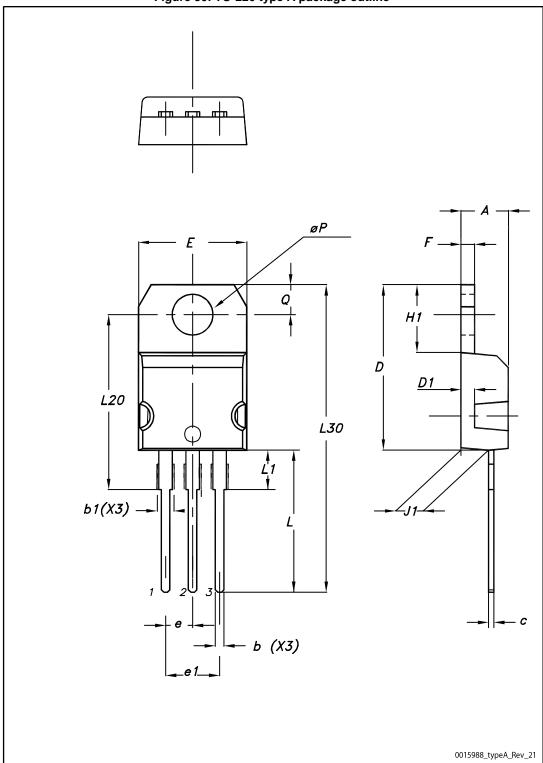


Table 14: TO-220 type A mechanical data

Table 14. 10-220 type A mechanical data					
Dim.	mm				
	Min.	Тур.	Max.		
А	4.40		4.60		
b	0.61		0.88		
b1	1.14		1.55		
С	0.48		0.70		
D	15.25		15.75		
D1		1.27			
Е	10.00		10.40		
е	2.40		2.70		
e1	4.95		5.15		
F	1.23		1.32		
H1	6.20		6.60		
J1	2.40		2.72		
L	13.00		14.00		
L1	3.50		3.93		
L20		16.40			
L30		28.90			
øΡ	3.75		3.85		
Q	2.65		2.95		

5 Revision history

Table 15: Document revision history

Date	Revision	Changes	
29-Jun-2010	1	First release.	
09-Sep-2010	2	Some values changed in Table 2.	
22-Dec-2010	3	Document status promoted from preliminary data to datasheet.	
24-Sep-2013	4	Added device in TO-220. Updated <i>Table 1: Device summary</i> , <i>Table 3: Thermal data</i> and <i>Section 4: Package mechanical data</i> accordingly.	
19-Sep-2016	5	Added the order codes STGB3HF60HD and STGF3HF60HD. Added TO-220FP and D ² PAK packages. Updated <i>Table 1: "Device summary"</i> , <i>Section 1: "Electrical ratings"</i> , <i>Section 4: "Package information"</i> . Minor text changes.	

IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2016 STMicroelectronics - All rights reserved

